



# BUK9M11-40H

N-channel 40 V, 11.0 mΩ logic level MOSFET in LPAK33

29 January 2019

Product data sheet

## 1. General description

Automotive qualified logic level N-channel MOSFET in an LPAK33 package using Trench 9 TrenchMOS technology. This product has been designed and qualified to AEC-Q101 for use in high performance automotive applications.

## 2. Features and benefits

- Fully automotive qualified to AEC-Q101 at 175 °C
- Trench 9 superjunction technology:
  - Low power losses, high power density
- LPAK copper clip package technology:
  - High robustness and reliability
  - Gull wing leads for high manufacturability and AOI
- Repetitive avalanche rated

## 3. Applications

- 12 V automotive systems
- Powertrain, chassis, body and infotainment applications
- Medium/Low power motor drive
- DC-DC systems
- LED lighting

## 4. Quick reference data

Table 1. Quick reference data

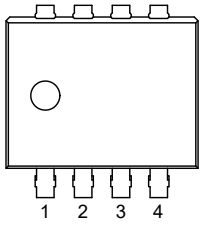
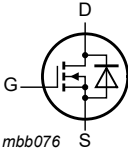
| Symbol                         | Parameter                        | Conditions                                                                                                                 | Min | Typ | Max | Unit |
|--------------------------------|----------------------------------|----------------------------------------------------------------------------------------------------------------------------|-----|-----|-----|------|
| $V_{DS}$                       | drain-source voltage             | $25\text{ °C} \leq T_j \leq 175\text{ °C}$                                                                                 | -   | -   | 40  | V    |
| $I_D$                          | drain current                    | $V_{GS} = 10\text{ V}$ ; $T_{mb} = 25\text{ °C}$ ; <a href="#">Fig. 2</a>                                                  | [1] | -   | 35  | A    |
| $P_{tot}$                      | total power dissipation          | $T_{mb} = 25\text{ °C}$ ; <a href="#">Fig. 1</a>                                                                           | -   | -   | 50  | W    |
| <b>Static characteristics</b>  |                                  |                                                                                                                            |     |     |     |      |
| $R_{DSon}$                     | drain-source on-state resistance | $V_{GS} = 10\text{ V}$ ; $I_D = 10\text{ A}$ ; $T_j = 25\text{ °C}$ ; <a href="#">Fig. 11</a>                              | 6.3 | 9   | 11  | mΩ   |
| <b>Dynamic characteristics</b> |                                  |                                                                                                                            |     |     |     |      |
| $Q_{GD}$                       | gate-drain charge                | $I_D = 10\text{ A}$ ; $V_{DS} = 20\text{ V}$ ; $V_{GS} = 4.5\text{ V}$ ; <a href="#">Fig. 13</a> ; <a href="#">Fig. 14</a> | -   | 1.6 | 3.2 | nC   |
| <b>Source-drain diode</b>      |                                  |                                                                                                                            |     |     |     |      |
| $Q_r$                          | recovered charge                 | $I_S = 10\text{ A}$ ; $dI_S/dt = -100\text{ A/}\mu\text{s}$ ; $V_{GS} = 0\text{ V}$ ; $V_{DS} = 20\text{ V}$               | -   | 13  | -   | nC   |

| Symbol | Parameter       | Conditions                                                                                                                                                | Min | Typ | Max | Unit |
|--------|-----------------|-----------------------------------------------------------------------------------------------------------------------------------------------------------|-----|-----|-----|------|
| S      | softness factor | $I_S = 10\text{ A}$ ; $dI_S/dt = -100\text{ A}/\mu\text{s}$ ; $V_{GS} = 0\text{ V}$ ; $V_{DS} = 20\text{ V}$ ; $T_j = 25\text{ }^\circ\text{C}$ ; Fig. 17 | -   | 0.6 | -   |      |

[1] 35A continuous current has been successfully demonstrated during application tests. Practically the current will be limited by PCB, thermal design and operating temperature.

## 5. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description                       | Simplified outline                                                                                        | Graphic symbol                                                                      |
|-----|--------|-----------------------------------|-----------------------------------------------------------------------------------------------------------|-------------------------------------------------------------------------------------|
| 1   | S      | source                            |  <p>LPAK33 (SOT1210)</p> |  |
| 2   | S      | source                            |                                                                                                           |                                                                                     |
| 3   | S      | source                            |                                                                                                           |                                                                                     |
| 4   | G      | gate                              |                                                                                                           |                                                                                     |
| mb  | D      | Mounting base; connected to drain |                                                                                                           |                                                                                     |

## 6. Ordering information

Table 3. Ordering information

| Type number | Package |                                                                                |         |
|-------------|---------|--------------------------------------------------------------------------------|---------|
|             | Name    | Description                                                                    | Version |
| BUK9M11-40H | LPAK33  | Plastic, single ended surface mounted package (LPAK33); 8 leads; 0.65 mm pitch | SOT1210 |

## 7. Marking

Table 4. Marking codes

| Type number | Marking code |
|-------------|--------------|
| BUK9M11-40H | 91140H       |

## 8. Limiting values

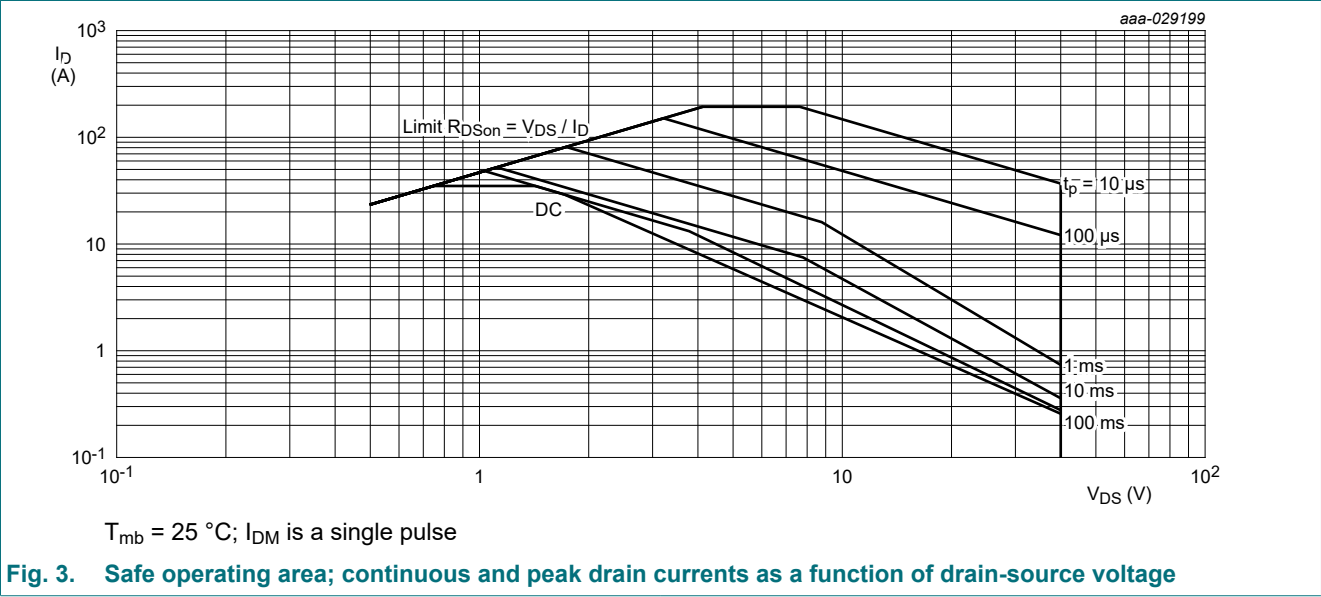
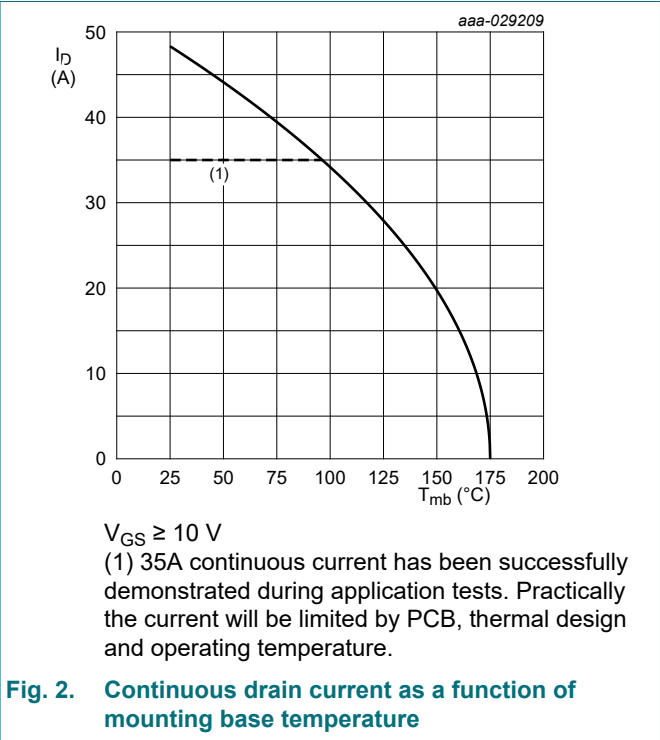
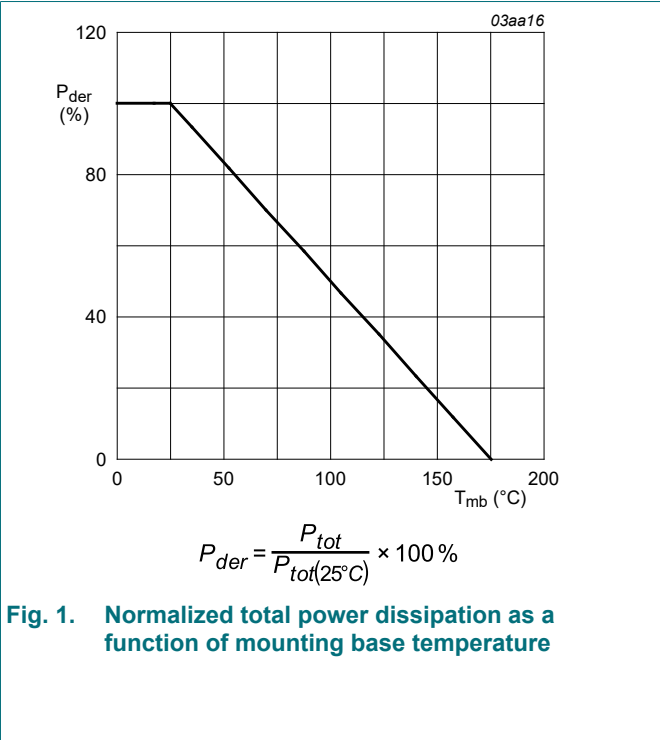
Table 5. Limiting values

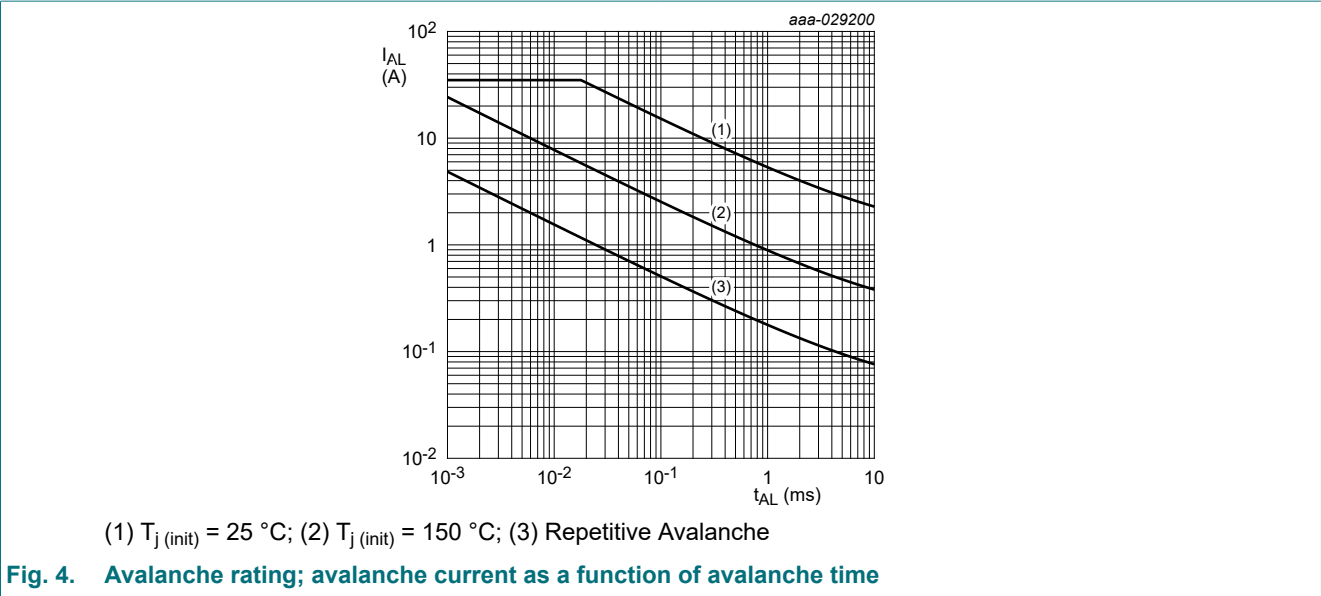
In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol             | Parameter               | Conditions                                                                              | Min | Max | Unit             |
|--------------------|-------------------------|-----------------------------------------------------------------------------------------|-----|-----|------------------|
| $V_{DS}$           | drain-source voltage    | $25\text{ }^\circ\text{C} \leq T_j \leq 175\text{ }^\circ\text{C}$                      | -   | 40  | V                |
| $V_{GS}$           | gate-source voltage     | DC; $T_j \leq 175\text{ }^\circ\text{C}$                                                | -10 | 16  | V                |
| $P_{tot}$          | total power dissipation | $T_{mb} = 25\text{ }^\circ\text{C}$ ; Fig. 1                                            | -   | 50  | W                |
| $I_D$              | drain current           | $V_{GS} = 10\text{ V}$ ; $T_{mb} = 25\text{ }^\circ\text{C}$ ; Fig. 2                   | [1] | 35  | A                |
|                    |                         | $V_{GS} = 10\text{ V}$ ; $T_{mb} = 100\text{ }^\circ\text{C}$ ; Fig. 2                  | -   | 34  | A                |
| $I_{DM}$           | peak drain current      | pulsed; $t_p \leq 10\text{ }\mu\text{s}$ ; $T_{mb} = 25\text{ }^\circ\text{C}$ ; Fig. 3 | -   | 193 | A                |
| $T_{stg}$          | storage temperature     |                                                                                         | -55 | 175 | $^\circ\text{C}$ |
| $T_j$              | junction temperature    |                                                                                         | -55 | 175 | $^\circ\text{C}$ |
| Source-drain diode |                         |                                                                                         |     |     |                  |

| Symbol               | Parameter                                    | Conditions                                                                                                                                      |         | Min | Max | Unit |
|----------------------|----------------------------------------------|-------------------------------------------------------------------------------------------------------------------------------------------------|---------|-----|-----|------|
| I <sub>S</sub>       | source current                               | T <sub>mb</sub> = 25 °C                                                                                                                         |         | -   | 35  | A    |
| I <sub>SM</sub>      | peak source current                          | pulsed; t <sub>p</sub> ≤ 10 μs; T <sub>mb</sub> = 25 °C                                                                                         |         | -   | 193 | A    |
| Avalanche ruggedness |                                              |                                                                                                                                                 |         |     |     |      |
| E <sub>DS(AL)S</sub> | non-repetitive drain-source avalanche energy | I <sub>D</sub> = 35 A; V <sub>sup</sub> ≤ 40 V; R <sub>GS</sub> = 50 Ω; V <sub>GS</sub> = 10 V; T <sub>j(init)</sub> = 25 °C; unclamped; Fig. 4 | [2] [3] | -   | 16  | mJ   |

- [1] 35A continuous current has been successfully demonstrated during application tests. Practically the current will be limited by PCB, thermal design and operating temperature.
- [2] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C.
- [3] Refer to application note AN10273 for further information.

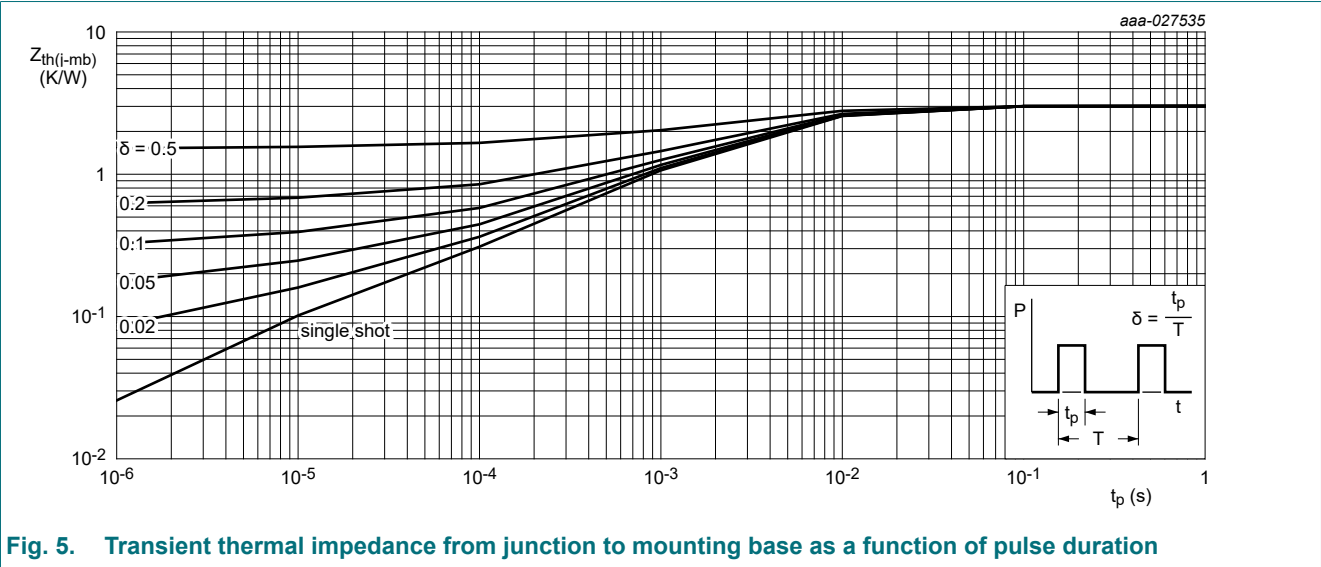




9. Thermal characteristics

Table 6. Thermal characteristics

| Symbol         | Parameter                                         | Conditions | Min | Typ | Max | Unit |
|----------------|---------------------------------------------------|------------|-----|-----|-----|------|
| $R_{th(j-mb)}$ | thermal resistance from junction to mounting base | Fig. 5     | -   | 2.8 | 3   | K/W  |



10. Characteristics

Table 7. Characteristics

| Symbol                        | Parameter                      | Conditions                                                                     | Min | Typ  | Max | Unit |
|-------------------------------|--------------------------------|--------------------------------------------------------------------------------|-----|------|-----|------|
| <b>Static characteristics</b> |                                |                                                                                |     |      |     |      |
| $V_{(BR)DSS}$                 | drain-source breakdown voltage | $I_D = 250\text{ }\mu\text{A}$ ; $V_{GS} = 0\text{ V}$ ; $T_j = 25\text{ °C}$  | 40  | 43   | -   | V    |
|                               |                                | $I_D = 250\text{ }\mu\text{A}$ ; $V_{GS} = 0\text{ V}$ ; $T_j = -40\text{ °C}$ | -   | 40.5 | -   | V    |

| Symbol                  | Parameter                        | Conditions                                                                                                                             |  | Min  | Typ  | Max  | Unit          |
|-------------------------|----------------------------------|----------------------------------------------------------------------------------------------------------------------------------------|--|------|------|------|---------------|
|                         |                                  | $I_D = 250\text{ }\mu\text{A}$ ; $V_{GS} = 0\text{ V}$ ; $T_j = -55\text{ }^\circ\text{C}$                                             |  | 36   | 40   | -    | V             |
| $V_{GS(th)}$            | gate-source threshold voltage    | $I_D = 1\text{ mA}$ ; $V_{DS}=V_{GS}$ ; $T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 9</a> ; <a href="#">Fig. 10</a>            |  | 1.5  | 1.85 | 2.2  | V             |
|                         |                                  | $I_D = 1\text{ mA}$ ; $V_{DS}=V_{GS}$ ; $T_j = -55\text{ }^\circ\text{C}$ ; <a href="#">Fig. 10</a>                                    |  | -    | -    | 2.6  | V             |
|                         |                                  | $I_D = 1\text{ mA}$ ; $V_{DS}=V_{GS}$ ; $T_j = 175\text{ }^\circ\text{C}$ ; <a href="#">Fig. 10</a>                                    |  | 0.7  | -    | -    | V             |
| $I_{DSS}$               | drain leakage current            | $V_{DS} = 40\text{ V}$ ; $V_{GS} = 0\text{ V}$ ; $T_j = 25\text{ }^\circ\text{C}$                                                      |  | -    | 0.01 | 5    | $\mu\text{A}$ |
|                         |                                  | $V_{DS} = 16\text{ V}$ ; $V_{GS} = 0\text{ V}$ ; $T_j = 125\text{ }^\circ\text{C}$                                                     |  | -    | 0.32 | 10   | $\mu\text{A}$ |
|                         |                                  | $V_{DS} = 40\text{ V}$ ; $V_{GS} = 0\text{ V}$ ; $T_j = 175\text{ }^\circ\text{C}$                                                     |  | -    | 23   | 500  | $\mu\text{A}$ |
| $I_{GSS}$               | gate leakage current             | $V_{GS} = 16\text{ V}$ ; $V_{DS} = 0\text{ V}$ ; $T_j = 25\text{ }^\circ\text{C}$                                                      |  | -    | 2    | 100  | nA            |
|                         |                                  | $V_{GS} = -10\text{ V}$ ; $V_{DS} = 0\text{ V}$ ; $T_j = 25\text{ }^\circ\text{C}$                                                     |  | -    | 2    | 100  | nA            |
| $R_{DSon}$              | drain-source on-state resistance | $V_{GS} = 10\text{ V}$ ; $I_D = 10\text{ A}$ ; $T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 11</a>                              |  | 6.3  | 9    | 11   | m $\Omega$    |
|                         |                                  | $V_{GS} = 10\text{ V}$ ; $I_D = 10\text{ A}$ ; $T_j = 105\text{ }^\circ\text{C}$ ; <a href="#">Fig. 12</a>                             |  | 8.6  | 12.9 | 16.5 | m $\Omega$    |
|                         |                                  | $V_{GS} = 10\text{ V}$ ; $I_D = 10\text{ A}$ ; $T_j = 125\text{ }^\circ\text{C}$ ; <a href="#">Fig. 12</a>                             |  | 9.5  | 14.1 | 17.7 | m $\Omega$    |
|                         |                                  | $V_{GS} = 10\text{ V}$ ; $I_D = 10\text{ A}$ ; $T_j = 175\text{ }^\circ\text{C}$ ; <a href="#">Fig. 12</a>                             |  | 11.5 | 16.9 | 21.3 | m $\Omega$    |
|                         |                                  | $V_{GS} = 4.5\text{ V}$ ; $I_D = 10\text{ A}$ ; $T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 11</a>                             |  | 7.9  | 11.3 | 14   | m $\Omega$    |
|                         |                                  | $V_{GS} = 4.5\text{ V}$ ; $I_D = 10\text{ A}$ ; $T_j = 105\text{ }^\circ\text{C}$ ; <a href="#">Fig. 12</a>                            |  | 10.8 | 16.1 | 21   | m $\Omega$    |
|                         |                                  | $V_{GS} = 4.5\text{ V}$ ; $I_D = 10\text{ A}$ ; $T_j = 125\text{ }^\circ\text{C}$ ; <a href="#">Fig. 12</a>                            |  | 11.9 | 17.4 | 22.6 | m $\Omega$    |
|                         |                                  | $V_{GS} = 4.5\text{ V}$ ; $I_D = 10\text{ A}$ ; $T_j = 175\text{ }^\circ\text{C}$ ; <a href="#">Fig. 12</a>                            |  | 14.4 | 21   | 27.2 | m $\Omega$    |
| $R_G$                   | gate resistance                  | $f = 1\text{ MHz}$ ; $T_j = 25\text{ }^\circ\text{C}$                                                                                  |  | 0.3  | 0.9  | 2.3  | $\Omega$      |
| Dynamic characteristics |                                  |                                                                                                                                        |  |      |      |      |               |
| $Q_{G(tot)}$            | total gate charge                | $I_D = 10\text{ A}$ ; $V_{DS} = 20\text{ V}$ ; $V_{GS} = 10\text{ V}$ ; <a href="#">Fig. 13</a> ; <a href="#">Fig. 14</a>              |  | -    | 15   | 21   | nC            |
|                         |                                  | $I_D = 10\text{ A}$ ; $V_{DS} = 20\text{ V}$ ; $V_{GS} = 4.5\text{ V}$ ; <a href="#">Fig. 13</a> ; <a href="#">Fig. 14</a>             |  | -    | 6.8  | 9.5  | nC            |
| $Q_{GS}$                | gate-source charge               |                                                                                                                                        |  | -    | 2.7  | 4.1  | nC            |
| $Q_{GD}$                | gate-drain charge                |                                                                                                                                        |  | -    | 1.6  | 3.2  | nC            |
| $C_{iss}$               | input capacitance                | $V_{DS} = 25\text{ V}$ ; $V_{GS} = 0\text{ V}$ ; $f = 1\text{ MHz}$ ; $T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 15</a>       |  | -    | 961  | 1345 | pF            |
| $C_{oss}$               | output capacitance               |                                                                                                                                        |  | -    | 273  | 382  | pF            |
| $C_{rss}$               | reverse transfer capacitance     |                                                                                                                                        |  | -    | 37   | 82   | pF            |
| $t_{d(on)}$             | turn-on delay time               | $V_{DS} = 20\text{ V}$ ; $R_L = 2\text{ }\Omega$ ; $V_{GS} = 4.5\text{ V}$ ; $R_{G(ext)} = 5\text{ }\Omega$                            |  | -    | 8.3  | -    | ns            |
| $t_r$                   | rise time                        |                                                                                                                                        |  | -    | 6.5  | -    | ns            |
| $t_{d(off)}$            | turn-off delay time              |                                                                                                                                        |  | -    | 9.5  | -    | ns            |
| $t_f$                   | fall time                        |                                                                                                                                        |  | -    | 4.5  | -    | ns            |
| Source-drain diode      |                                  |                                                                                                                                        |  |      |      |      |               |
| $V_{SD}$                | source-drain voltage             | $I_S = 10\text{ A}$ ; $V_{GS} = 0\text{ V}$ ; $T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 16</a>                               |  | -    | 0.83 | 1.2  | V             |
| $t_{rr}$                | reverse recovery time            | $I_S = 10\text{ A}$ ; $dI_S/dt = -100\text{ A}/\mu\text{s}$ ; $V_{GS} = 0\text{ V}$ ; $V_{DS} = 20\text{ V}$ ; <a href="#">Fig. 17</a> |  | -    | 20   | -    | ns            |
| $Q_r$                   | recovered charge                 | $I_S = 10\text{ A}$ ; $dI_S/dt = -100\text{ A}/\mu\text{s}$ ; $V_{GS} = 0\text{ V}$ ; $V_{DS} = 20\text{ V}$                           |  | -    | 13   | -    | nC            |

| Symbol | Parameter       | Conditions                                                                                                                                                                | Min | Typ  | Max | Unit |
|--------|-----------------|---------------------------------------------------------------------------------------------------------------------------------------------------------------------------|-----|------|-----|------|
| S      | softness factor | $I_S = 10\text{ A}$ ; $dI_S/dt = -100\text{ A}/\mu\text{s}$ ; $V_{GS} = 0\text{ V}$ ; $V_{DS} = 20\text{ V}$ ; $T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 17</a> | -   | 0.6  | -   |      |
|        |                 | $I_S = 10\text{ A}$ ; $dI_S/dt = -500\text{ A}/\mu\text{s}$ ; $V_{GS} = 0\text{ V}$ ; $V_{DS} = 20\text{ V}$ ; $T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 17</a> | -   | 0.32 | -   |      |

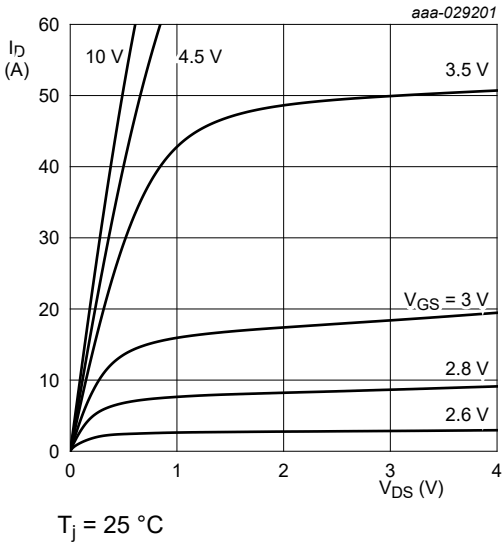


Fig. 6. Output characteristics; drain current as a function of drain-source voltage; typical values

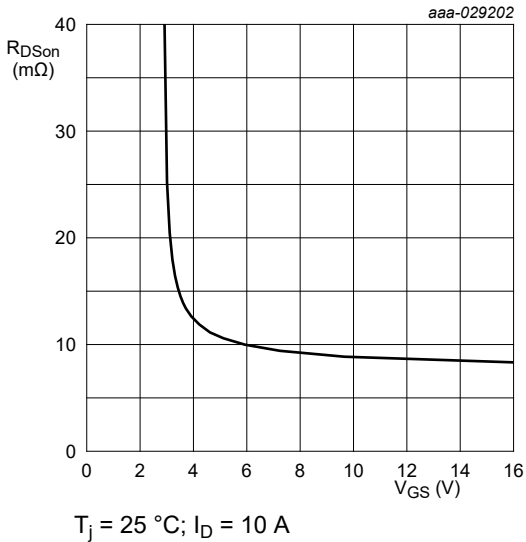


Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

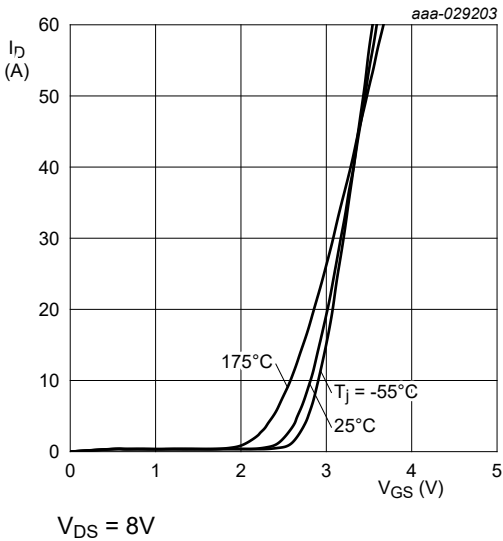


Fig. 8. Transfer characteristics; drain current as a function of gate-source voltage; typical values

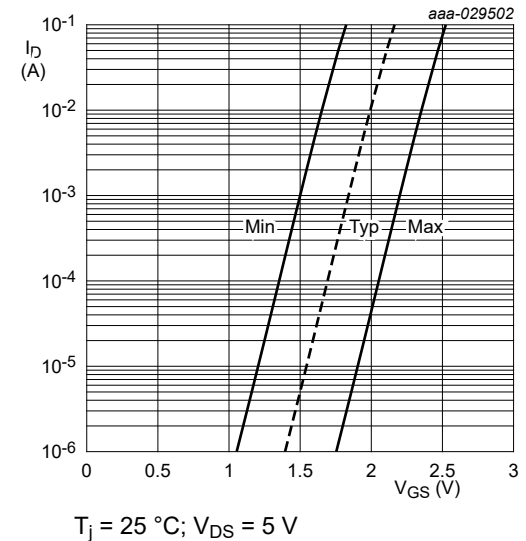


Fig. 9. Sub-threshold drain current as a function of gate-source voltage

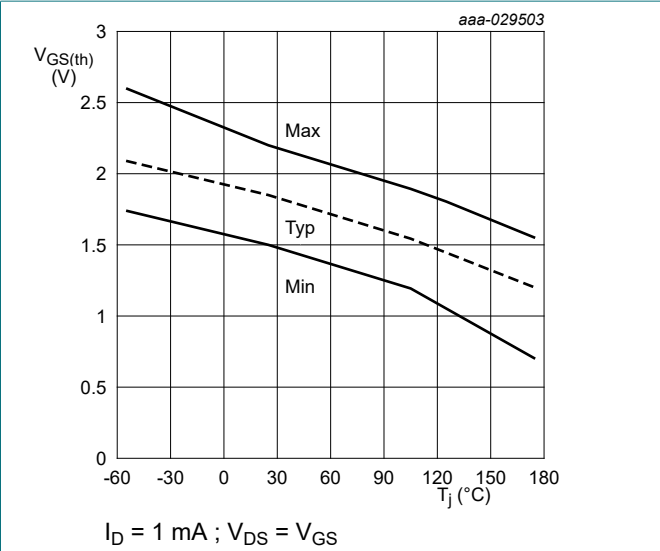


Fig. 10. Gate-source threshold voltage as a function of junction temperature

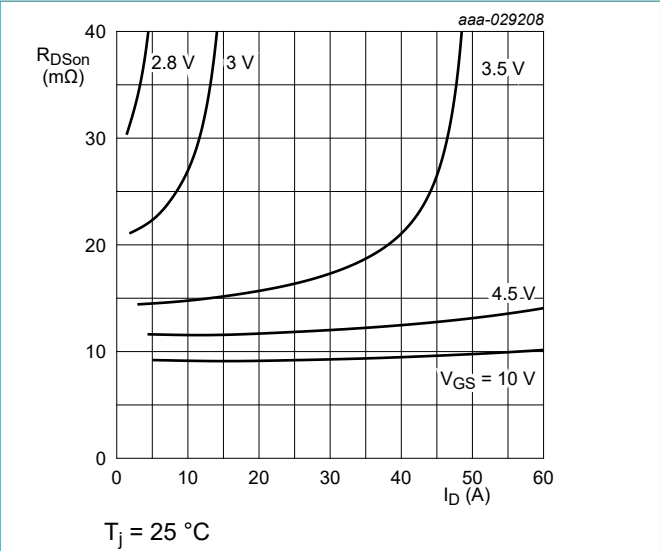


Fig. 11. Drain-source on-state resistance as a function of drain current; typical values

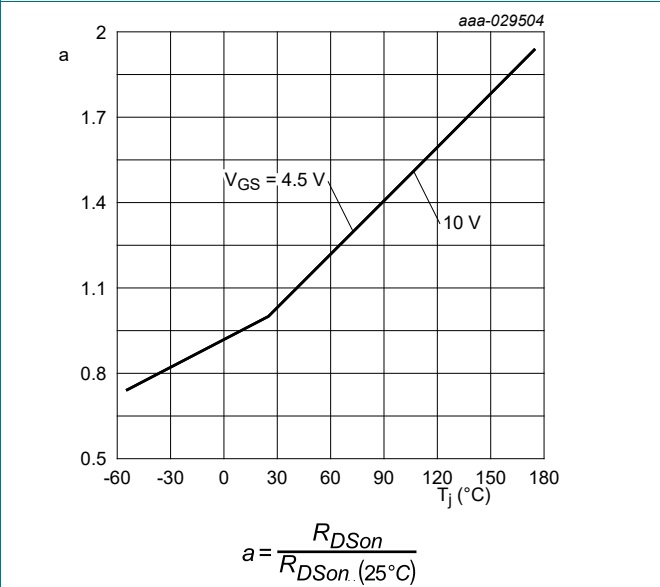


Fig. 12. Normalized drain-source on-state resistance factor as a function of junction temperature

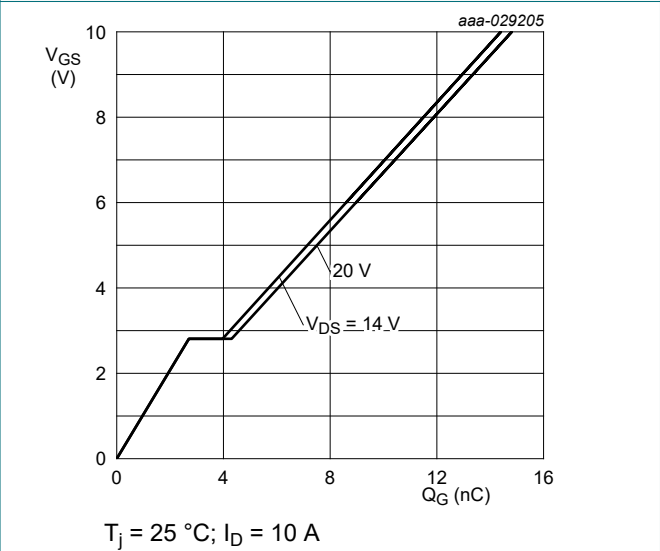
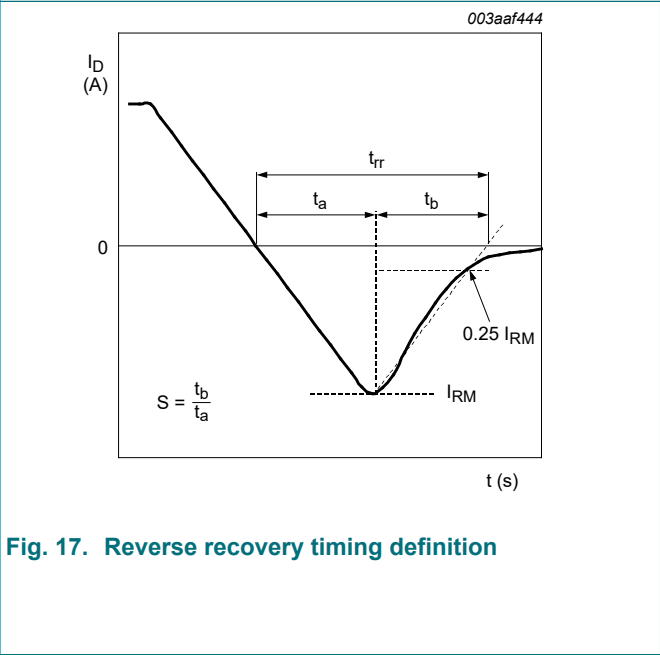
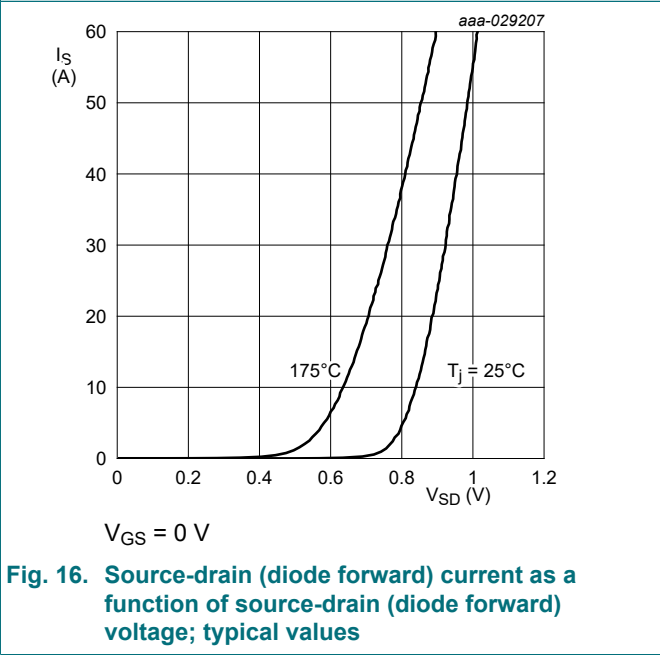
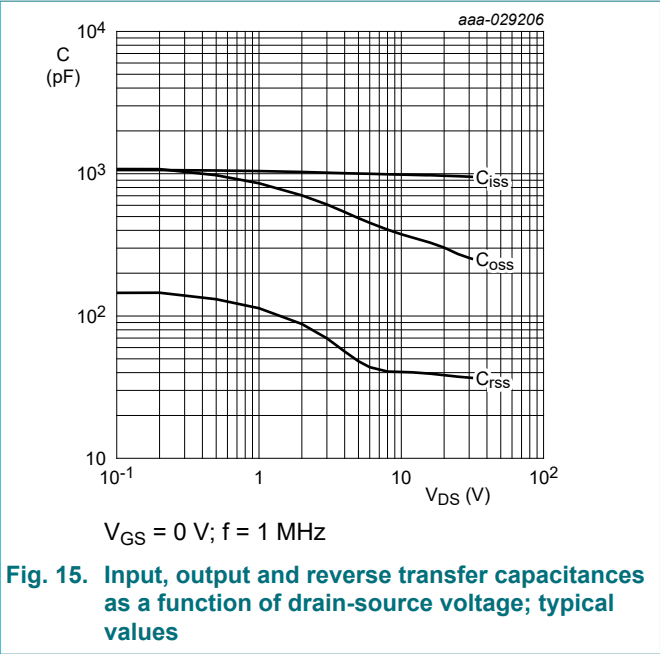
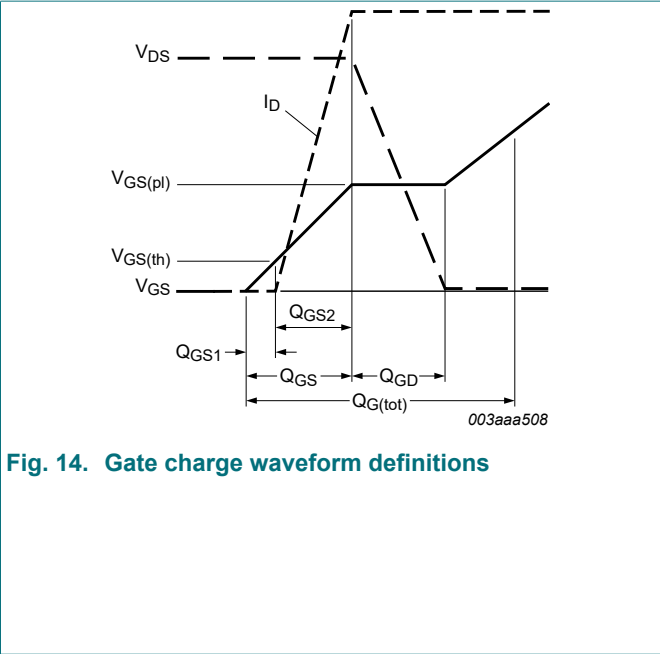


Fig. 13. Gate-source voltage as a function of gate charge; typical values



11. Package outline

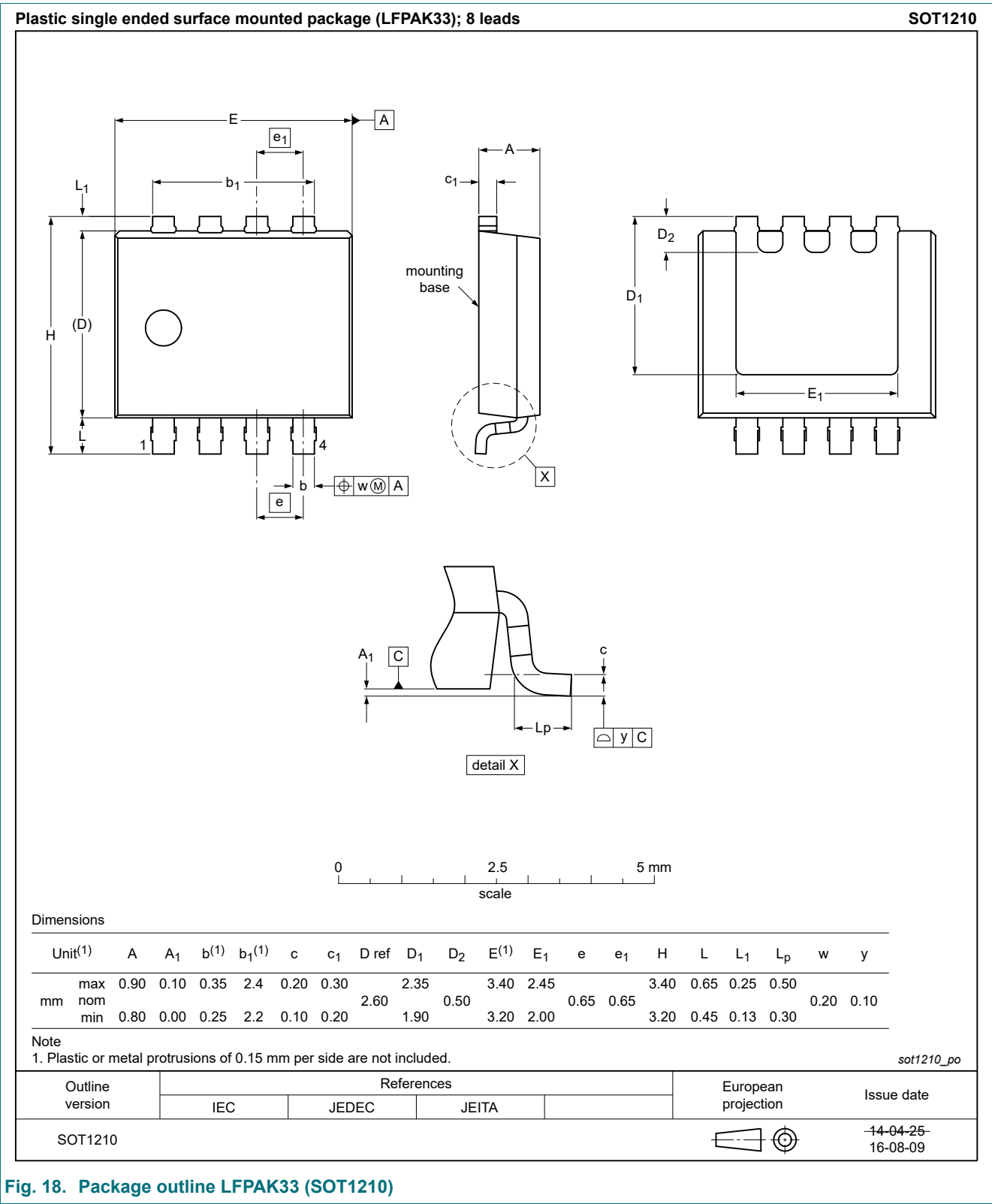


Fig. 18. Package outline LPAK33 (SOT1210)

## 12. Legal information

### Data sheet status

| Document status<br>[1][2]      | Product status [3] | Definition                                                                            |
|--------------------------------|--------------------|---------------------------------------------------------------------------------------|
| Objective [short] data sheet   | Development        | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet | Qualification      | This document contains data from the preliminary specification.                       |
| Product [short] data sheet     | Production         | This document contains the product specification.                                     |

- [1] Please consult the most recently issued document before initiating or completing a design.
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